SANGDEST MICROELECTRONICS

Technical Data Data Sheet N0189, Rev. A

MBRF10100CT SCHOTTKY RECTIFIER

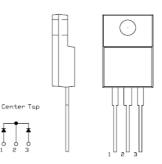
Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

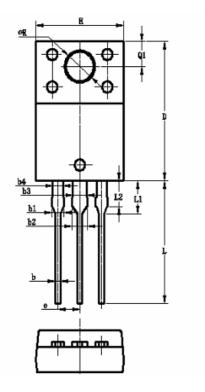
Features:

- 150 °C T J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- · Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In mm



OUTLINE DRAWING



	OPTION 1(CJ)		OPTION 2(HD)	
Dim	Min	Max	Min	Max
Α	4.35	4.65	4.30	4.70
b	0.50	0.75	0.50	0.75
b1	1.15	1.402	1.20	1.45
b2	1.55	1.802	1.60	1.85
b3	1.55	1.65	1.50	1.75
b4	1.10	1.35	1.10	1.35
С	0.50	0.75	0.55	0.75
D	14.8	15.2	14.80	15.20
Е	10.06	10.26	9.96	10.36
е	2.46	2.62	2.55TYP	
F	2.85	3.15	2.80	3.20
G	6.50	6.90	6.50	6.90
L	12.70	13.70	12.70	13.70
L1	3.40	3.80	3.40	4.00
L2	2.60	3.00	-	-
Q	2.60	2.80	2.50	2.90
Q1	2.50	2.90	2.50	2.90
ØR	3.40	3.60	3.30	3.70

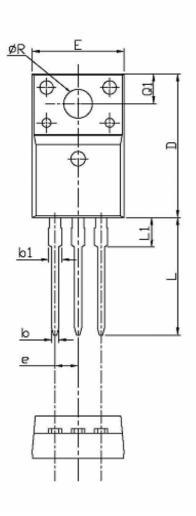
Weiqi Street, Airport Development Zone, Jiangning District, Nanjing, China 211113 (86) 25-87123907 •
FAX (86) 25-87123900 • World Wide Web Site - http://www.sangdest.com.cn • E-Mail Address - sales@ sangdest.com.cn •

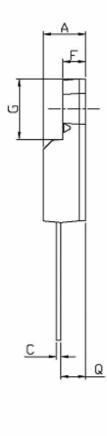
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Green Products



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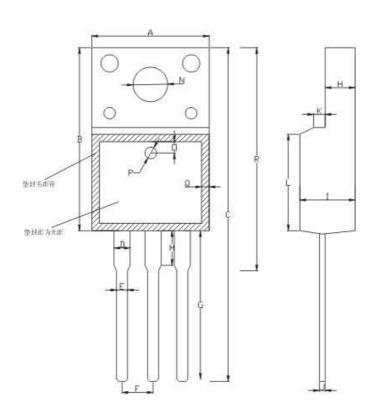


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	OPTION 3		OPTION 4	
Dim	Min	Max	Min	Max
Α	4.53	4.93	4.50	4.90
b	0.71	0.91	0.70	0.90
b1	1.15	1.39	1.33	1.47
С	0.36	0.53	0.45	0.60
D	15.67	16.07	15.67	16.07
Е	9.96	10.36	9.96	10.36
e	2.54TYP		2.54 BSC	
F	2.34	2.76	2.34	2.74
G	6.50	6.90	6.48	6.88
L	12.37	12.77	12.78	13.18
L1	2.23	2.63	3.03	3.43
Q	2.56	2.96	2.56	2.96
Q1	3.10	3.50	3.10	3.50
ØR	2.98	3.38	3.08	3.28

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A:10.20	± 0.50	B:15.90	± 0.50	C:29.00	± 1.00	D:1.24	± 0.10
E:0.80	± 0.10	F:2.54	± 0.10	G:13.10	$\pm 1,0$	H:2.55	± 0.05
I:4.70	± 0.05	J:0.50	± 0.05	K:1.20	± 0.20	L:8.00	± 0.50
M:3.00	± 0.50	N:3.20	± 0.20	O:1,25	± 0.05	P:1.5	± 0.05
Q:1.0	±0.20	R:19.2	± 1.0				

OPTION 5 (SR)

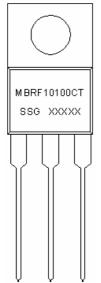
ITO-220AB



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Marking Diagram:



Cautions: Molding resin Epoxy resin UL:94V-0

Ordering Information:

Where	XXXXX	is	YYWWL

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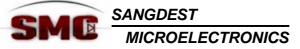
MBR	= Device Type
F	= Package type
10	= Forward Current (10A)
100	= Reverse Voltage (100V)
CT	= Configuration
SSG	= SSG
ΥY	= Year
WW	= Week
L	= Lot Number

Device	Package	Shipping
MBRF10100CT	ITO-220AB (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V _{RWM}	-	100	V
Max. Average Forward	I _{F(AV)}	50% duty cycle @T _C =105 °C rectangular wave form	10	А
Max. Peak One Cycle Non- Repetitive Surge Current (per leg)	I _{FSM}	8.3 ms, half Sine pulse	120	А



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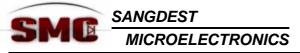
Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V _{F1}	@ 5A, Pulse, T _J = 25 °C	0.85	V
(per leg) *	V_{F2}	@ 5A, Pulse, T _J = 125 °C	0.75	V
Max. Reverse Current at DC condition (per leg)	I _{R1}	$@V_R = rated V_R$ T _J = 25 °C	1.0	mA
Max. Reverse Current (per leg) *	I _{R2}	$@V_R = rated V_R$ T _J = 125 °C	15	mA
Max. Junction Capacitance (per leg)	C⊤	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	300	pF
Typical Series Inductance (per leg)	L _S	Measured lead to lead 5 mm from package body	8.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/µs
RSM Isolation Voltage (t = 1.0 second, R. H. < =30%, $T_A = 25 \text{ °C}$)	V _{ISO}	Clip mounting, the epoxy body away from the heatsink edge by more than 0.110" along the lead direction.	4500	V
	V ISO	Clip mounting, the epoxy body is inside the heatsink.	3500	v
		Screw mounting, the epoxy body is inside the heatsink.	1500	

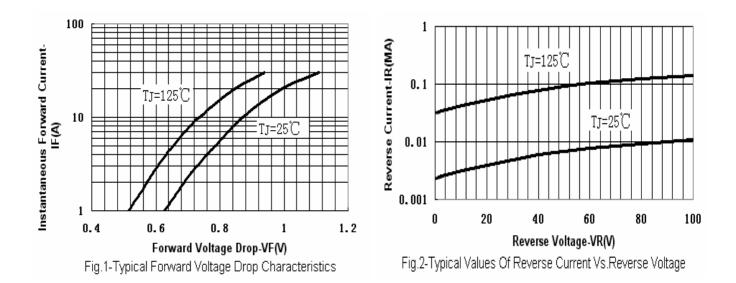
* Pulse Width < 300µs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units	
Max. Junction Temperature	TJ	-	-55 to +150	°C	
Max. Storage Temperature	T _{stg}	-	-55 to +150	°C	
Maximum Thermal Resistance Junction to Case (per leg)	$R_{ extsf{ heta}JC}$	DC operation	4.5	°C/W	
Approximate Weight	wt	-	2	g	
Case Style	ITO-220AB				



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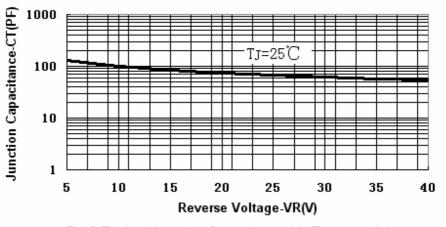


Fig.3-Typical Junction Capacitance Vs.Reverse Voltage



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